

Abstract of Disclosure**NONVOLATILE MEMORY AND METHOD OF PROGRAMMING THE SAME**

A nonvolatile memory cell includes a floating gate; a programming region, having a first current path connected to the floating gate, for programming by providing charge carriers to the floating gate through the first current path or extracting charge carriers stored in the floating gate; and a verification region, having a second current path different from the first current path, for verifying the charge amount of the floating gate through the second current path during programming.

Figure 3A